TOSHIBA

Preliminary

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L53S

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

• Two devices are built into the sES6 package, which is smaller and thinner than the super-thin and ultra-super-mini (6-pin) ES6 package.

Mounted Devices

	Q1: SSM (TESM)	Q2: TESM
Three-pin (SSM/TESM) product No.	MT3S06S (MT3S06T)	MT3S05T

Maximum Ratings (Ta = 25°C)

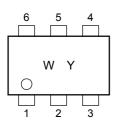
Characteristics	Symbol	Q1	Q2	Unit		
Collector-base voltage	V _{CBO}	10	10	V		
Collector-emitter voltage	V _{CEO}	5	5	V		
Emitter-base voltage	V _{EBO}	1.5	2	V		
Collector current	Ι _C	15	40	mA		
Base current	Ι _Β	7	10	mA		
Collector power dissipation	P _C (Note 1)	150		mW		
Junction temperature	Tj	125		125		°C
Storage temperature range	T _{stg}	-55~125		°C		

1.COLLECTOR1 4.BASE2				
2.EMITTER1 5.EMITTER2				
3.COLLECTOR2 6.BASE1				
JEDEC —				
JEITA —				
TOSHIBA 2-2Q1A				

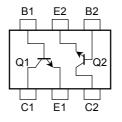
Weight: 2.1 mg (typ.)

Note 1: Total power dissipation of Q1 and Q2 mounted on the circuit board

Marking



Pin Connections



Electrical Characteristics Q1-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0$	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$	_	_	1	μA
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	70	_	140	_
Transition frequency	f _T	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	7	10		GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	7.5		dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 7 \text{ mA}, \text{ f} = 2 \text{ GHz}$	4.5	8.3		
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 3 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 3 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	1.6	3	uВ
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ (Note 2)		0.35	0.75	pF

Electrical Characteristics Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0$	—		0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 V, I_{C} = 0$	_		1	μA
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	80		140	_
Transition frequency	f _T	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	2	4.5	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	7.5	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 20 \text{ mA}, \text{ f} = 1 \text{ GHz}$	7.5	10.5	_	ub
Noise figure	NF	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	1.4	2.2	dB
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ (Note 2)		0.95	1.15	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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